

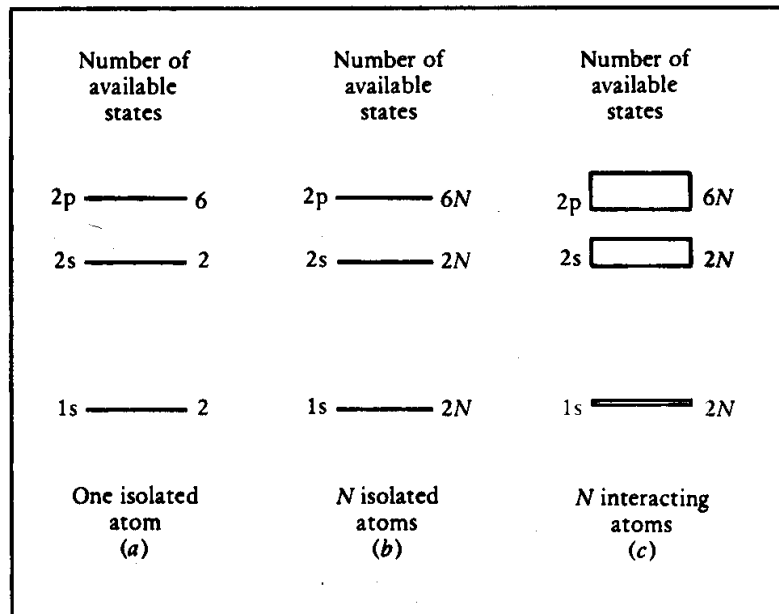
Qualitative Picture of the Ideal Diode

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UC San Diego MAE 119

Lecture Notes

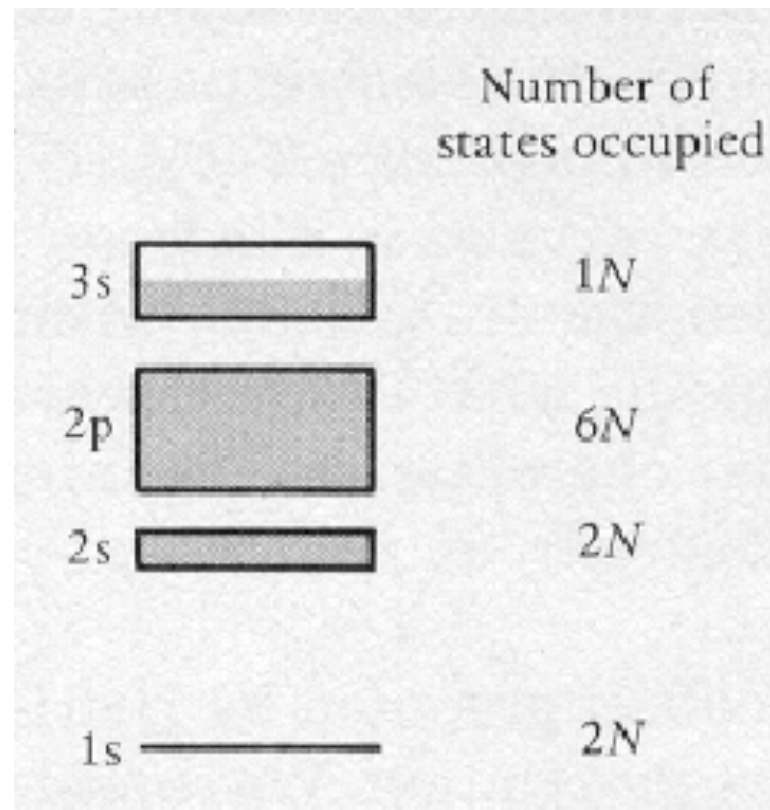
Band Theory of Solids: From Single Atoms...to Solid Crystals



- Isolated Li atom (conducting metal)
 - Has well-defined, isolated allowable electron energy levels
- N isolated atoms
 - $N \times$ isolated atom levels
- Strongly interacting Li atoms
 - Interaction shifts (or splits) individual **energy bands** into isolated regions separated by **forbidden bands**

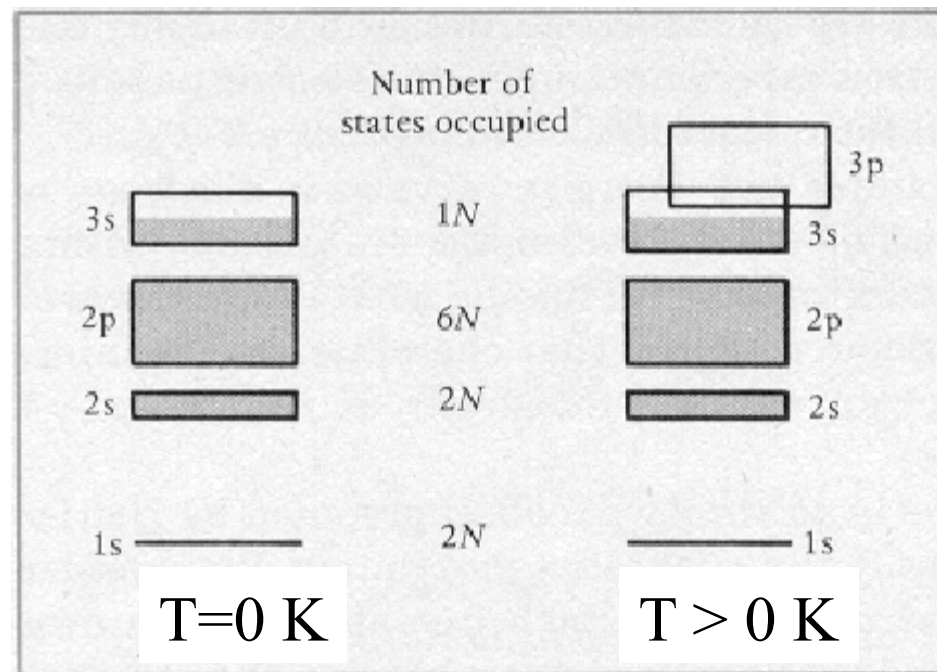
Band Theory of Solids: Conductors

- Next, consider N interacting sodium atoms at 0 deg K
 - Electrons in config $1s^2 2s^2 2p^6 3s^1$
 - Shells filled to 3s, which has 1 electron

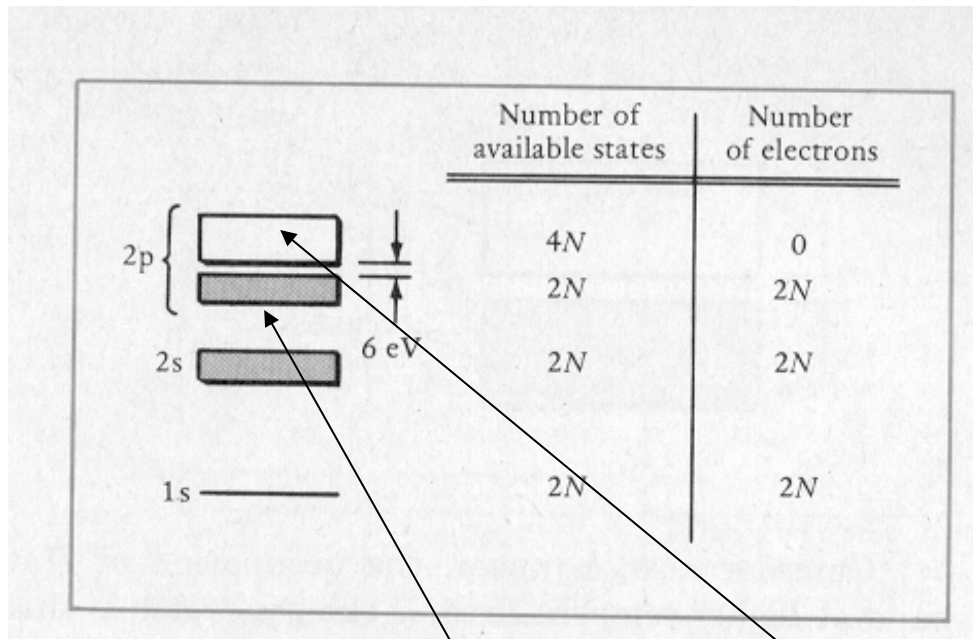


Band Theory of Solids: Conductors

- Next, consider N interacting sodium atoms w/ $T > 0$
 - Electrons in config $1s^2 2s^2 2p^6 3s^1$
 - Shells filled to $3s$, which has 1 electron
 - This Valence electron is weakly bound \Rightarrow if T High enough can move to mobile state \rightarrow conductor!



Band Theory of Solids: Insulators

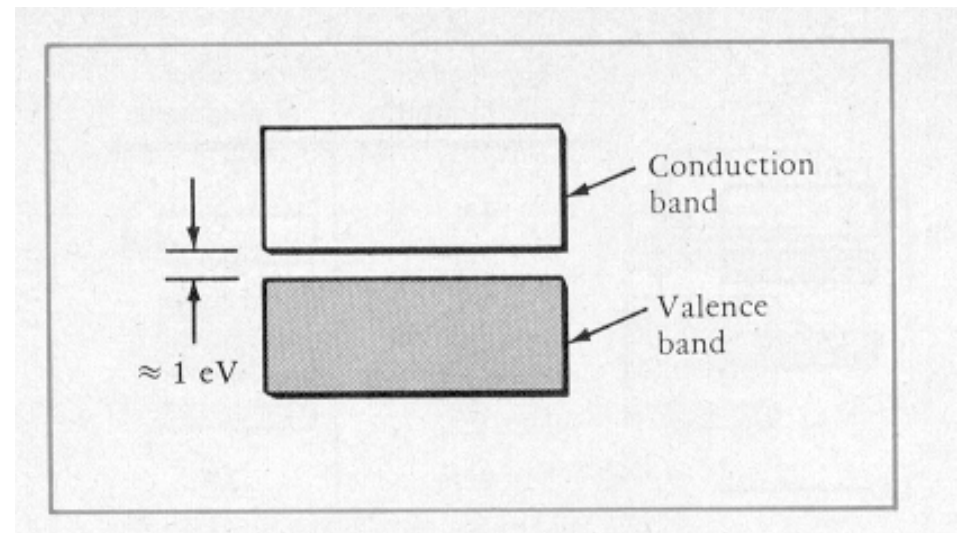


Lower levels: VALENCE BAND
Upper levels: CONDUCTION BAND

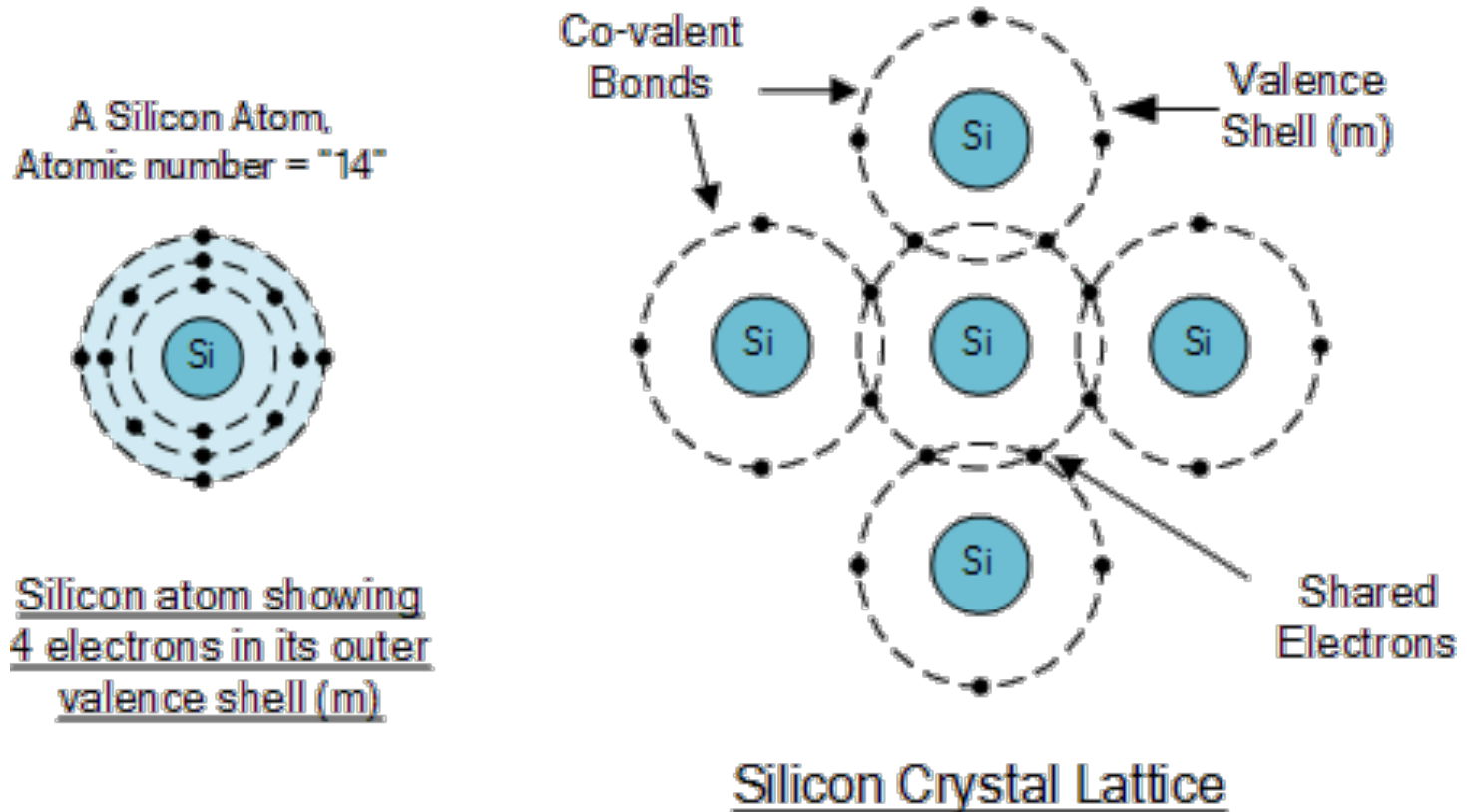
- Carbon in Diamond Form
 - Electrons in $1s^2 2s^2 2p^2$ State
 - 2p band has 2N electrons, but 6N states
 - BUT... crystal structure splits 2p into two distinct bands
 - **BAND GAP is ~ 6 eV**
 \gg Temperature
(~ 0.02 - 0.1 eV)
Thus...Diamond is
An Insulator

Band Theory of Solids: Semiconductors

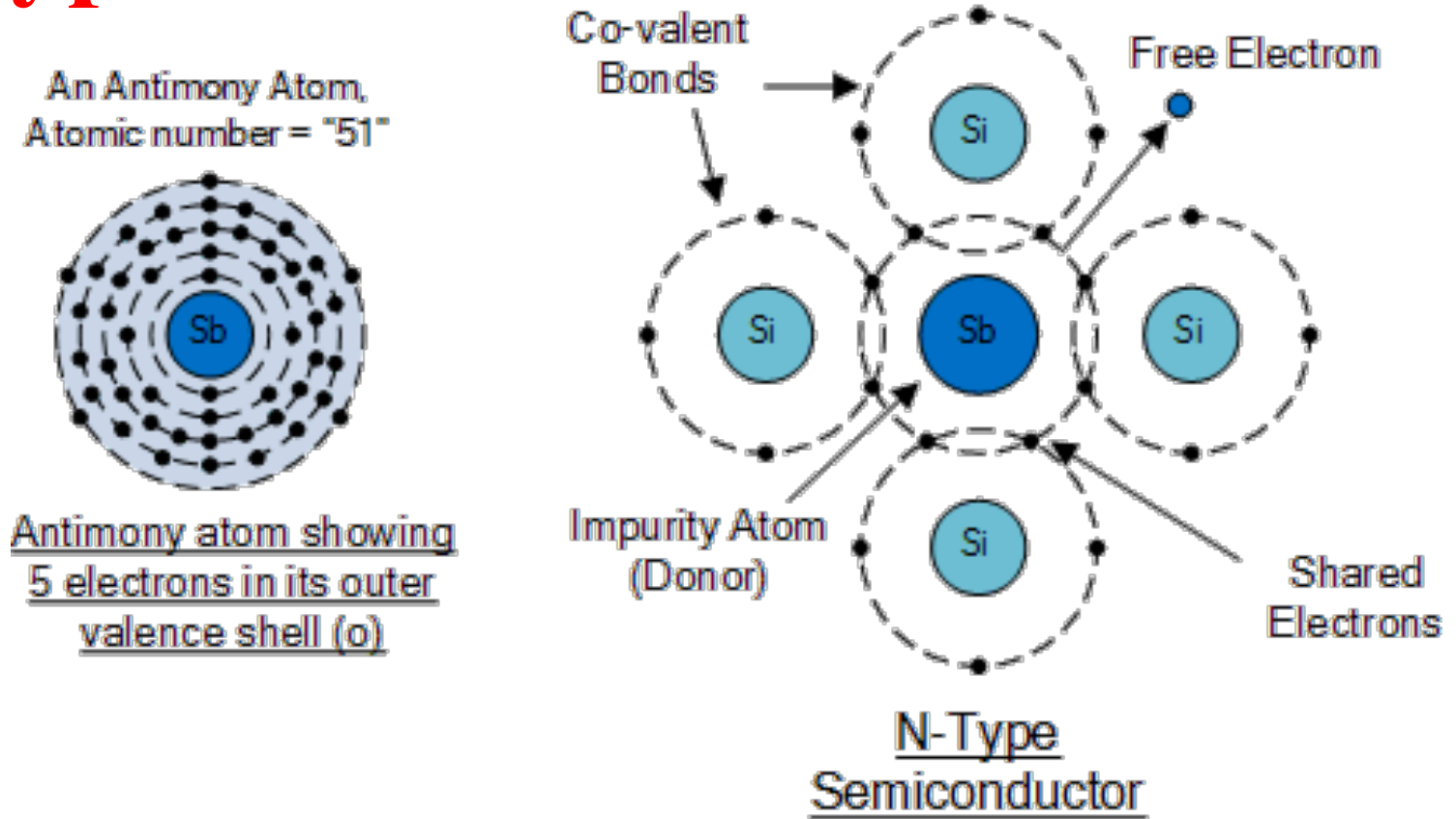
- *Some crystalline materials have smaller band-gap energy*
- At low temperatures behave like insulators
 - $E_{bg} \sim 1\text{eV} \gg \text{Temperature}$
- With an electric field
 - Electrons gain energy
 - Can move into upper (conduction) band



Si as a Semiconductor Material

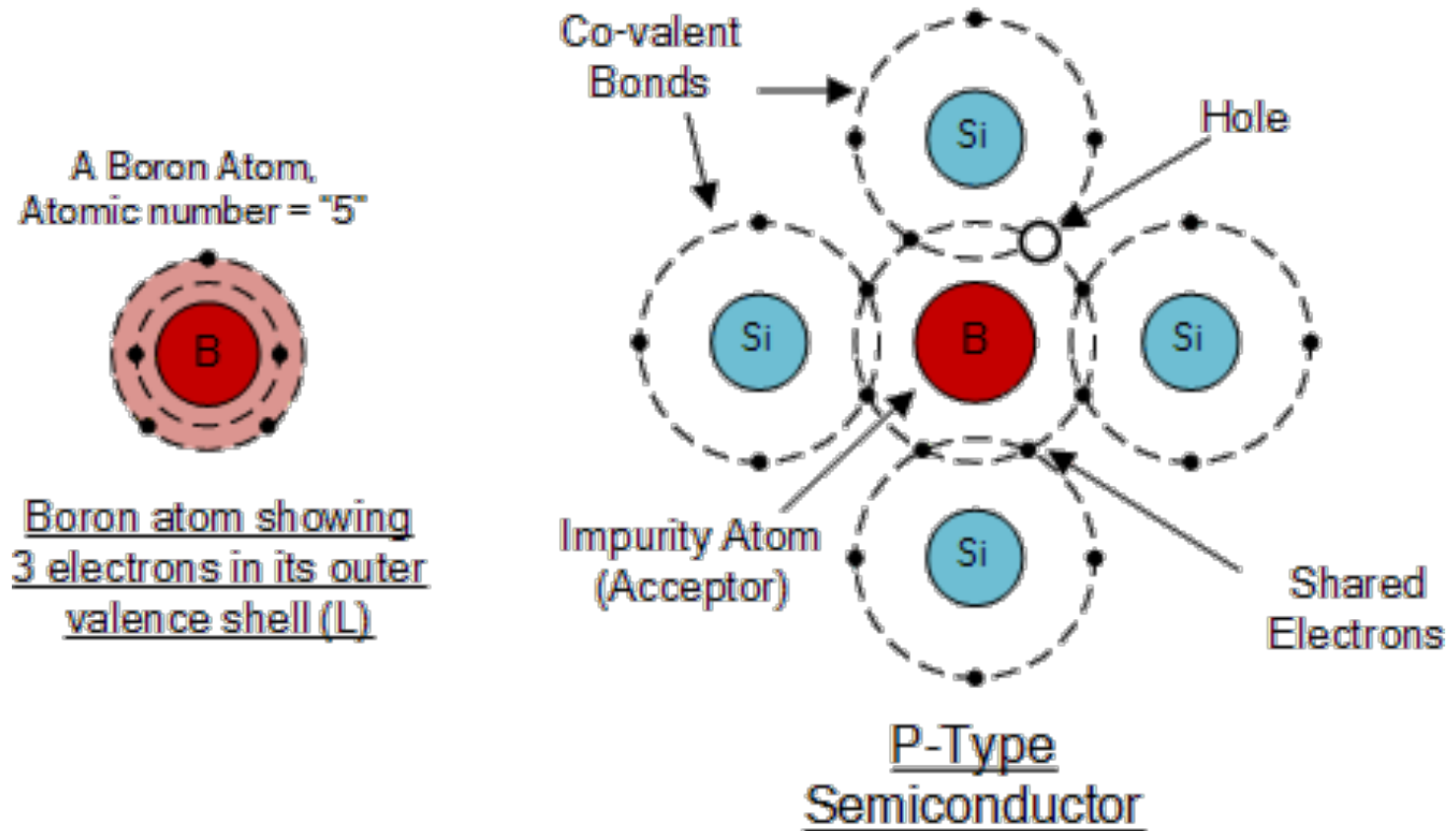


N-type Semiconductor Materials



N-type Si has an extra electron for each dopant atom,
This electron is mobile

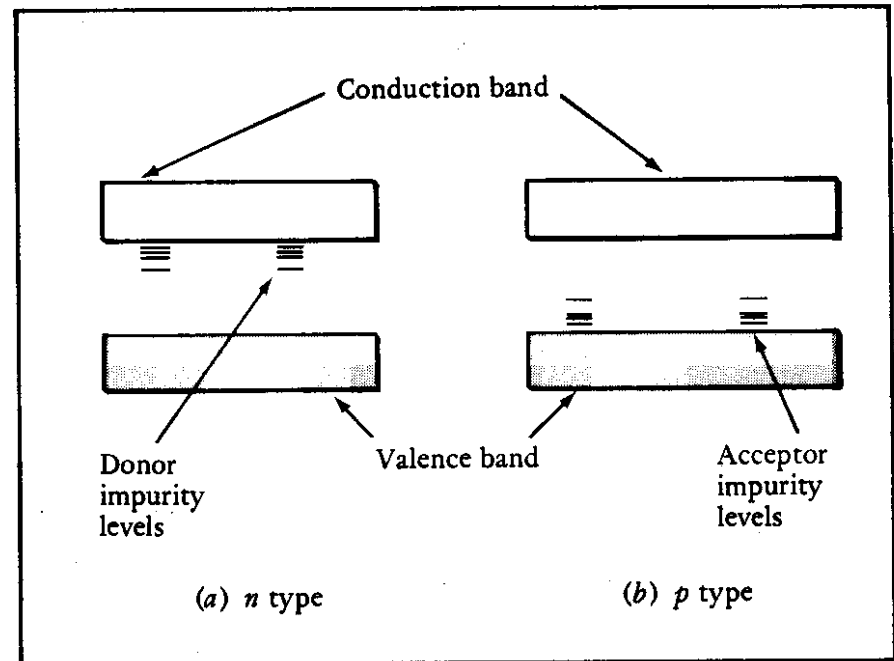
P-type Semiconductor Materials



P-type Si has a “hole” (i.e a missing electron) that acts like
A mobile positive charge

Dopants create allowed energy states between the pure material valence and conduction bands

- Pure semiconductor matl's conduction and valence bands separated by E_{gap}
- In pure materials this gap has no allowed states -> no particles in these energy ranges
- IF ADD donor or acceptor impurities then this creates allowed states between the pure-material conduction & valence bands



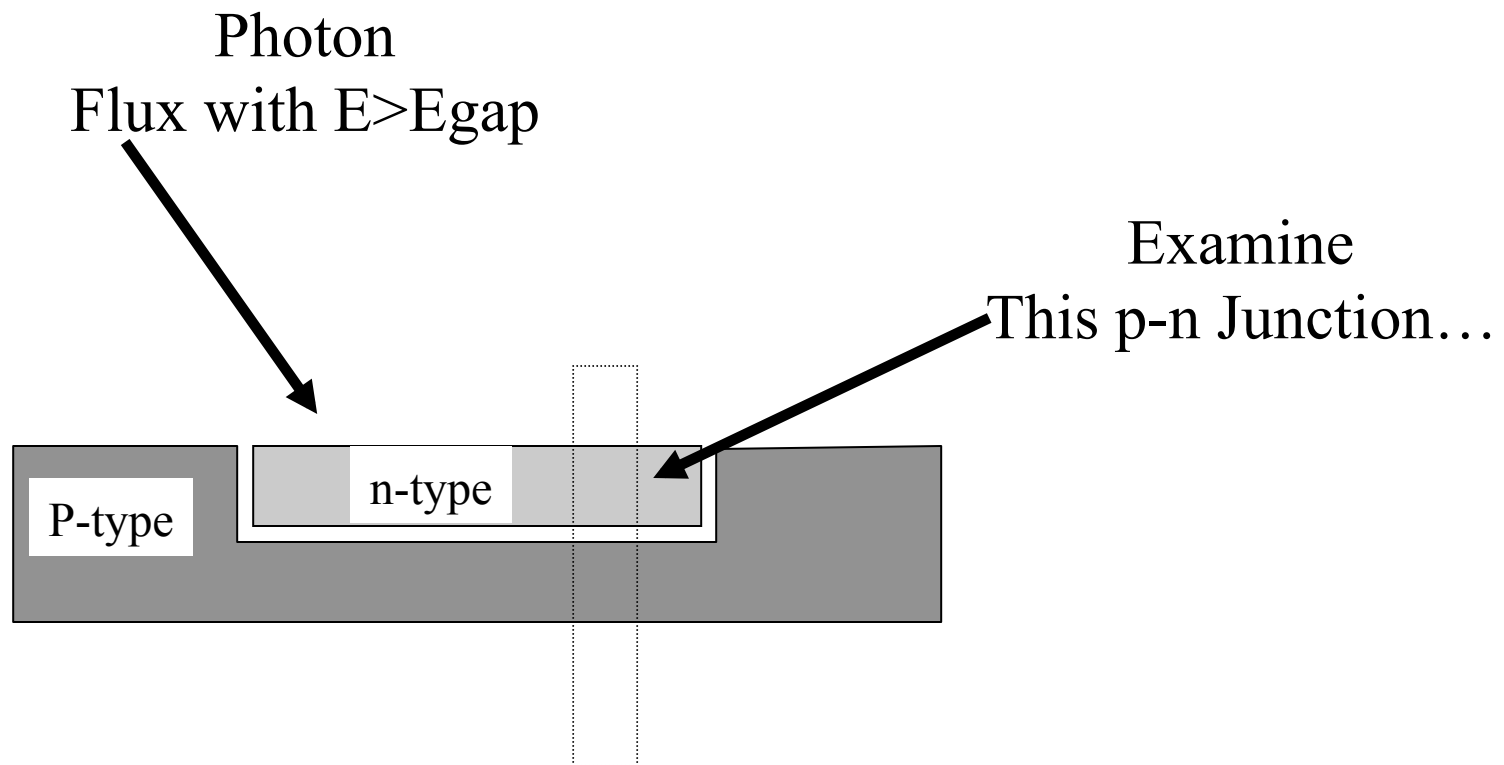
Basics of Solar PV Cells

- Key Concepts
 - Un-illuminated p-n junction diode
 - Photon Energy Spectrum
 - Charge Carrier Generation Via Photon Absorption
 - Charge Carrier Loss Mechanisms
 - Illuminated p-n junction diode: The Solar PV Cell
 - Solar PV Cell' s as an Electricity Source

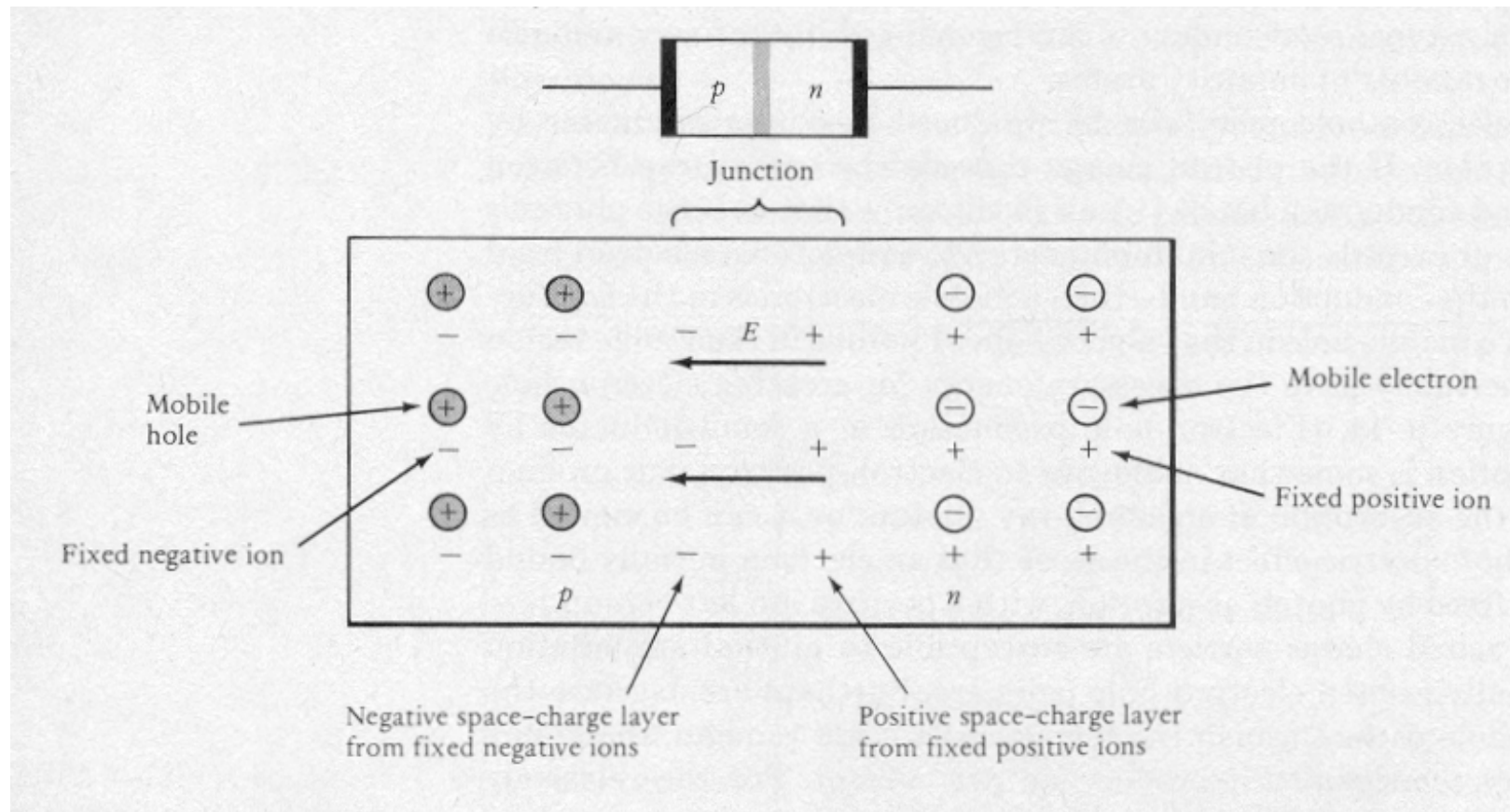
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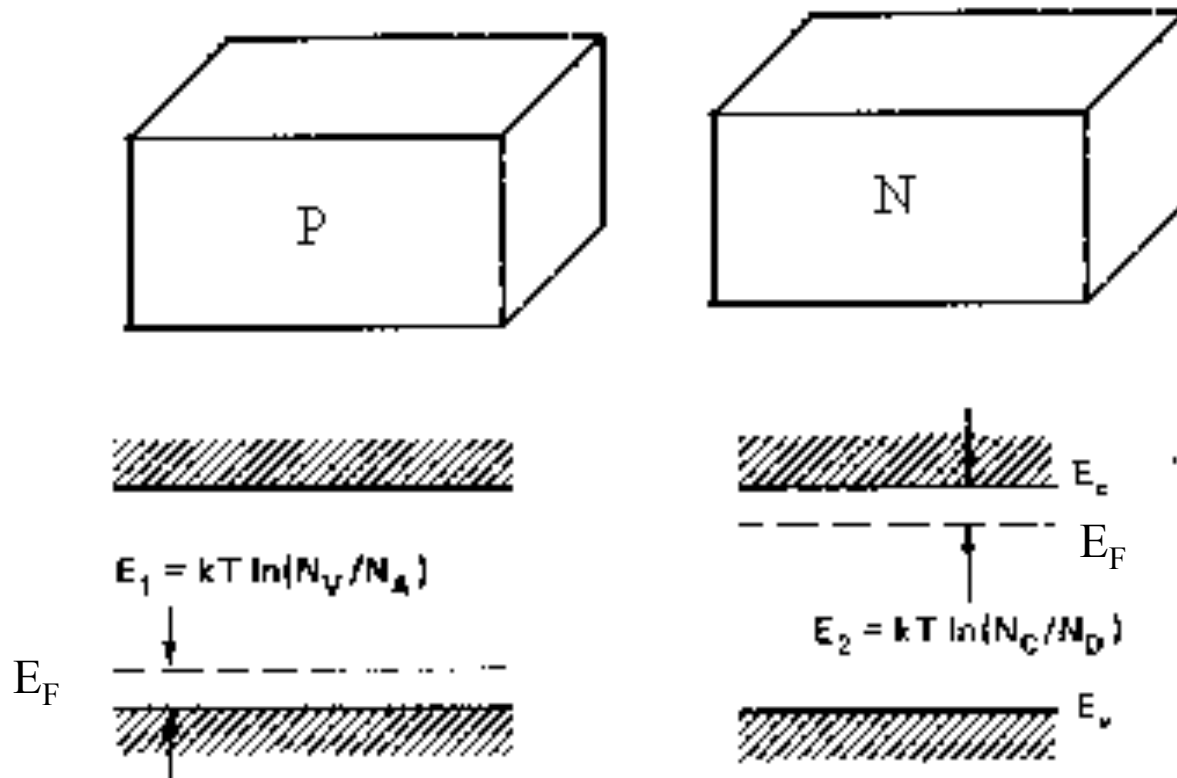
A Solar PV Cell is just a p-n junction (“diode”) illuminated by light....



Simplified Model of PV Cell: No Light



Conduction Band & Valence Band Energy Levels in SEPARATE p-type and n-type materials



Conduction Band & Valence Band Energy Levels in *p-n junction*

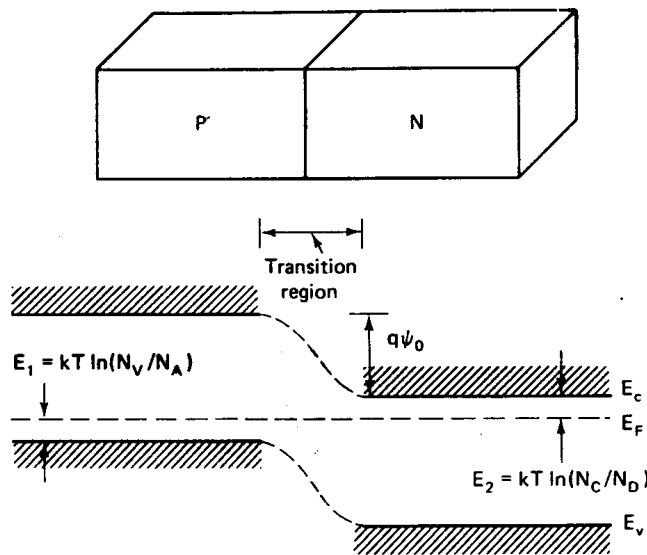
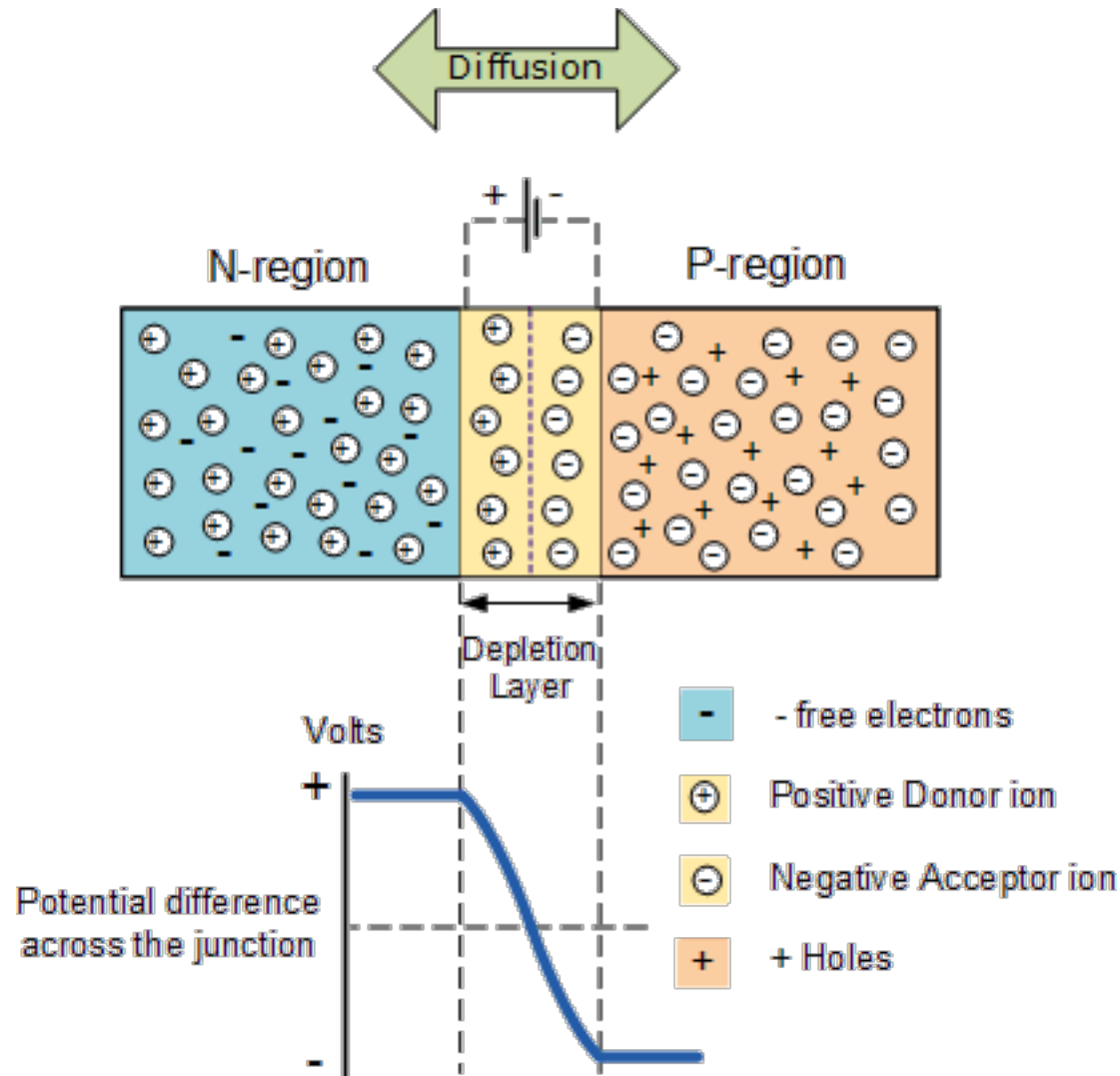


Figure 4.3. A *p-n* junction formed by bringing the isolated *p*-type and *n*-type regions together. Also shown is the corresponding energy-band diagram at thermal equilibrium.

- THERE CAN ONLY BE ONE FERMI ENERGY IN A SYSTEM AT EQUIL (!)
- Result:

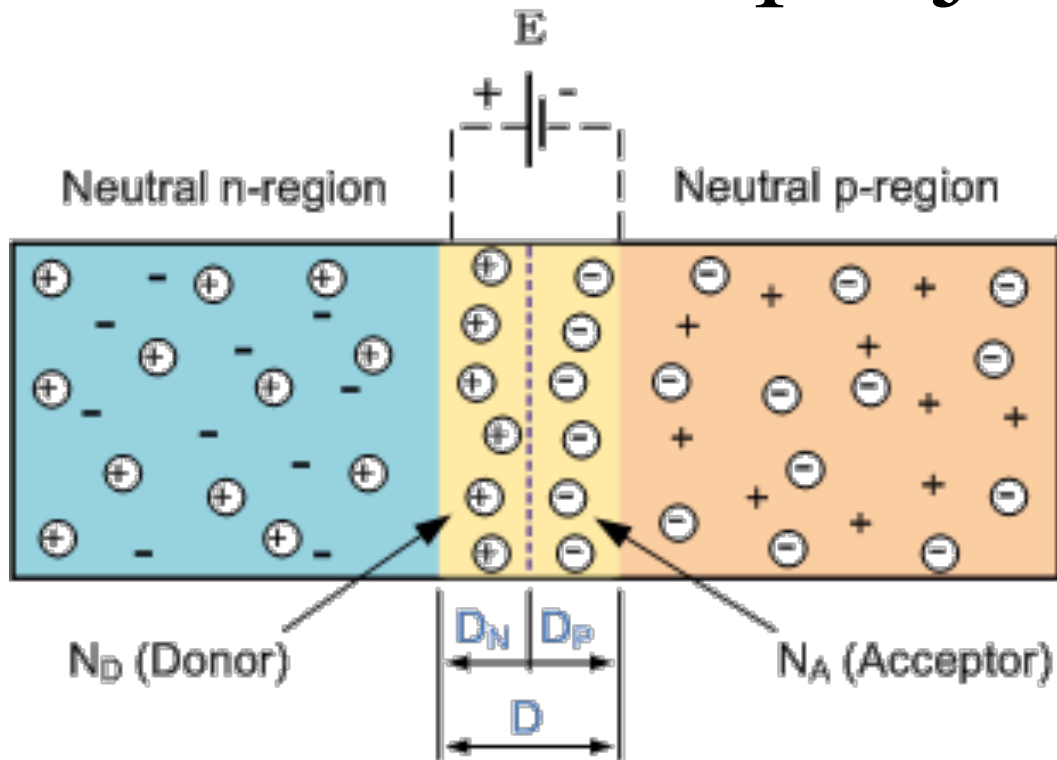
$$\psi_0 = \frac{kT}{q} \ln \left(\frac{N_A N_D}{n_i^2} \right)$$

P-N Junction formed by joining p & n type materials



- Concentration gradient of n and p densities leads to diffusion of mobile electrons into the p-region, and mobile holes into the n-type region.
- This leaves behind immobile positive donor ions in n-region (N_{D+}) and negative acceptor (N_{A-}) ions in p-region
- Process stops when sufficiently large potential gradient develops

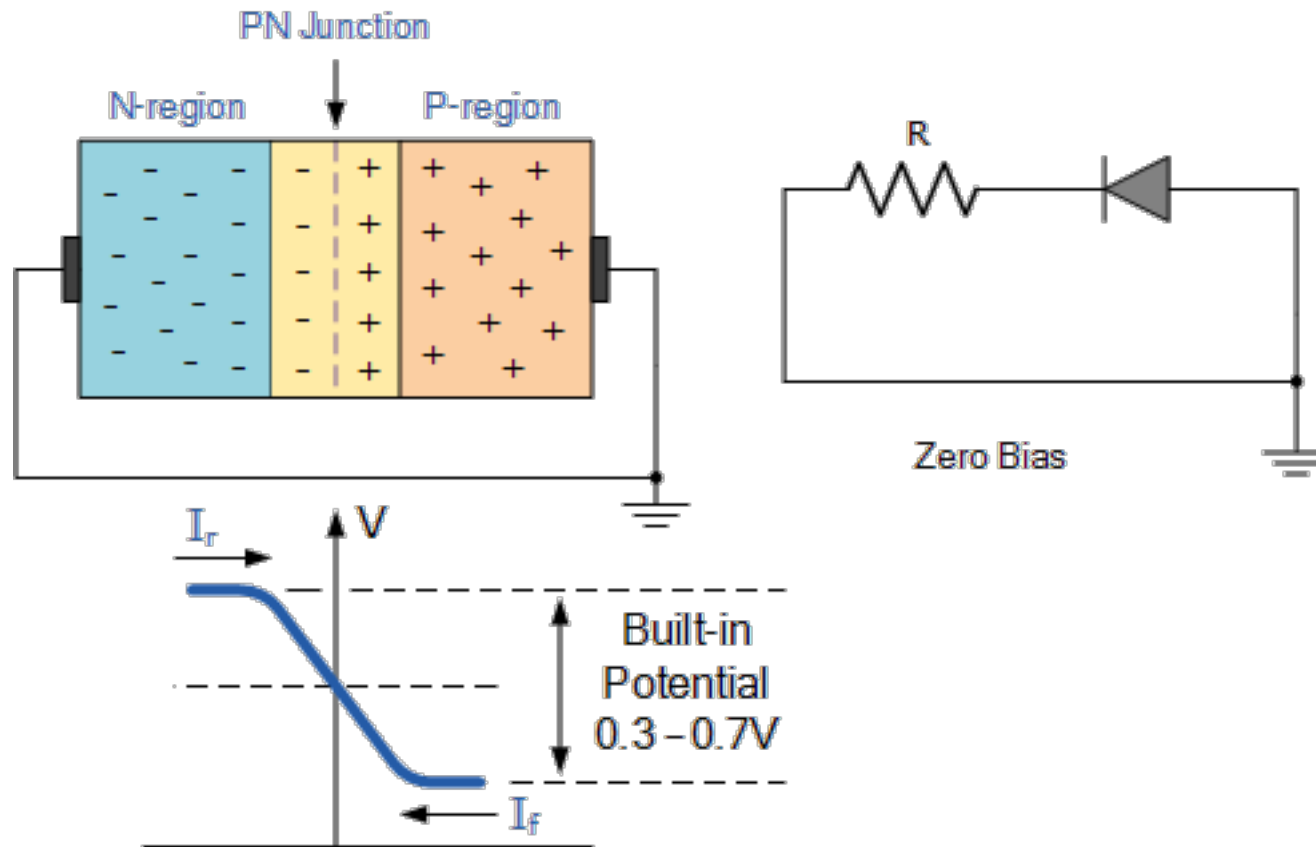
Equilibrium potential develops across the p-n junction



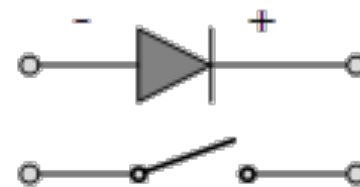
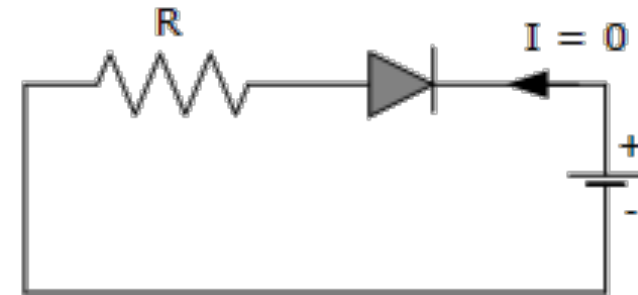
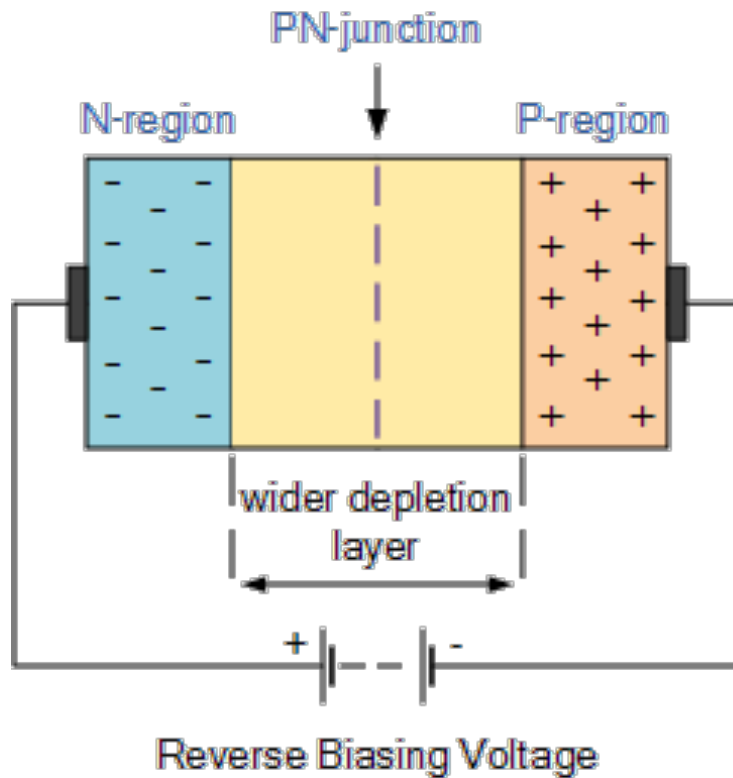
Get an electric field naturally occurring across junction

$$E_o = V_T \ln \left(\frac{N_D \cdot N_A}{n_i^2} \right)$$

Now connect p and n regions via external circuit



Connecting w/ext. circuit and adding an external bias that **ADDS** to natural bias (**“Reverse”** bias) widens depletion zone



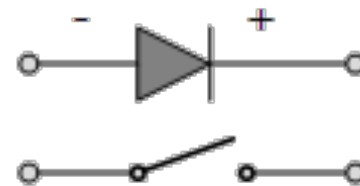
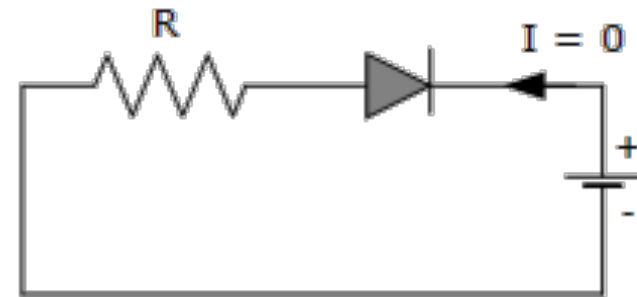
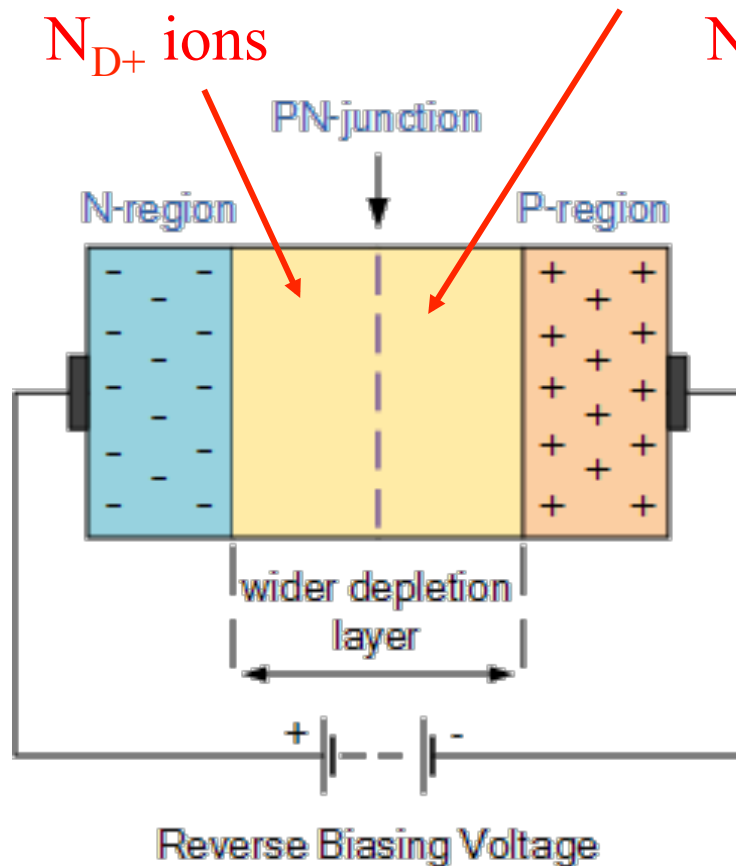
Connecting w/ext. circuit and adding an external bias that **ADDS** to natural bias (**“Reverse”** bias) widens depletion zone

Uncover more
un-neutralized

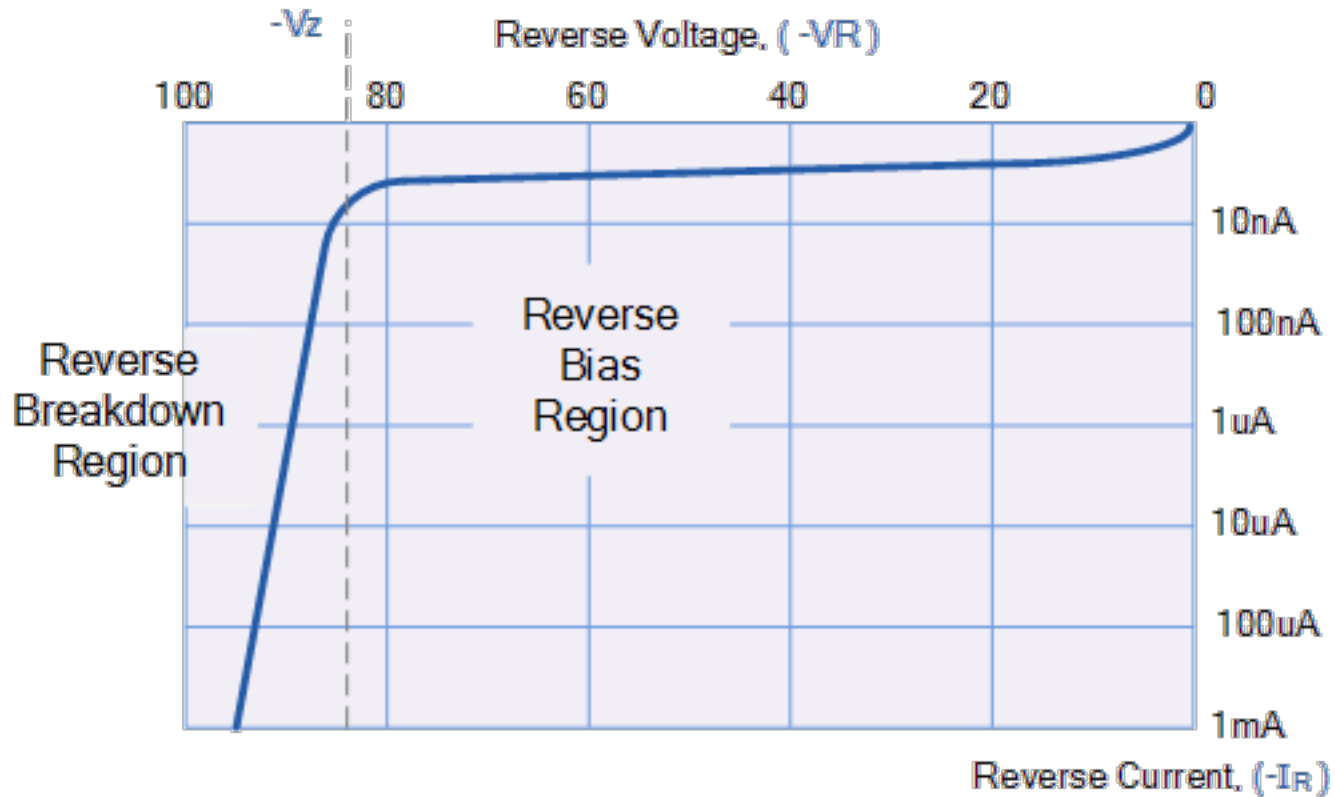
N_{D+} ions

Uncover more
un-neutralized

N_{A-} ions

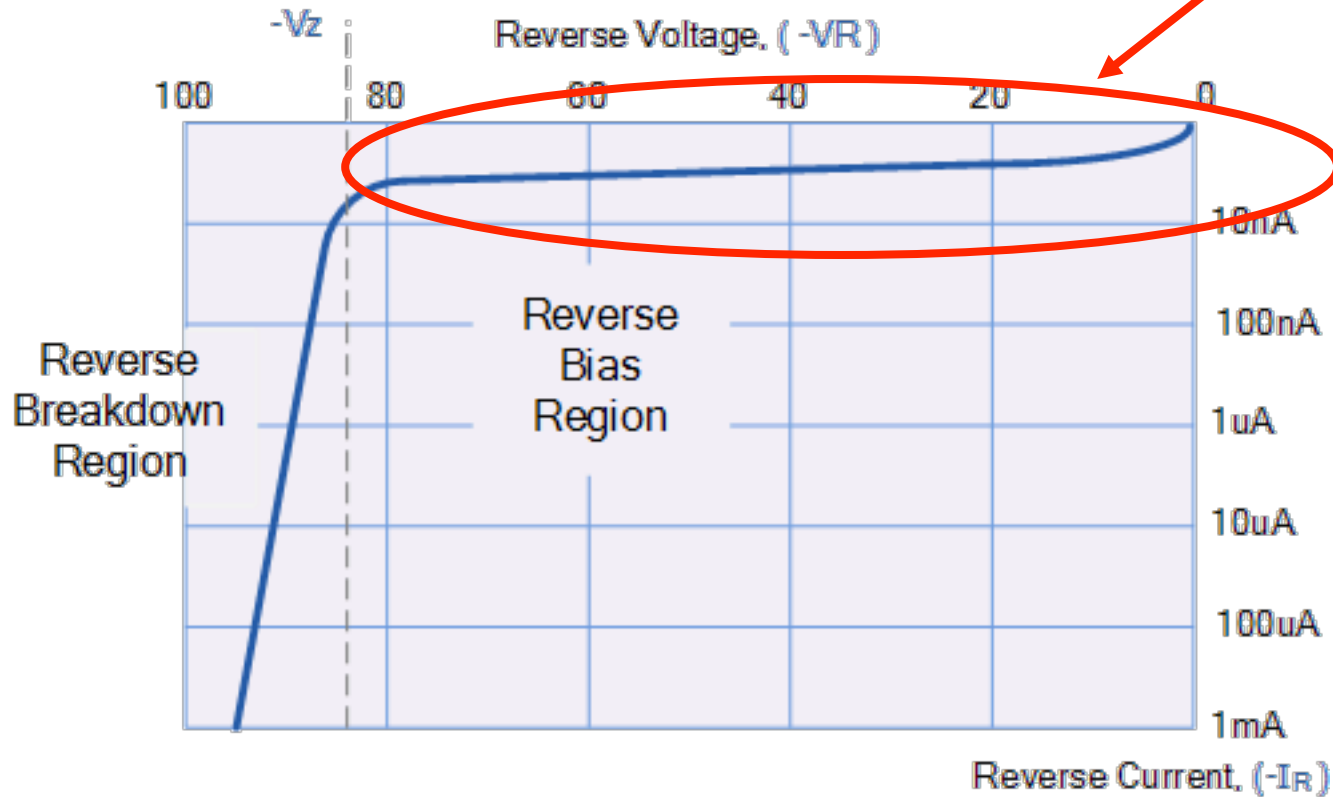


Current-voltage response for reverse bias

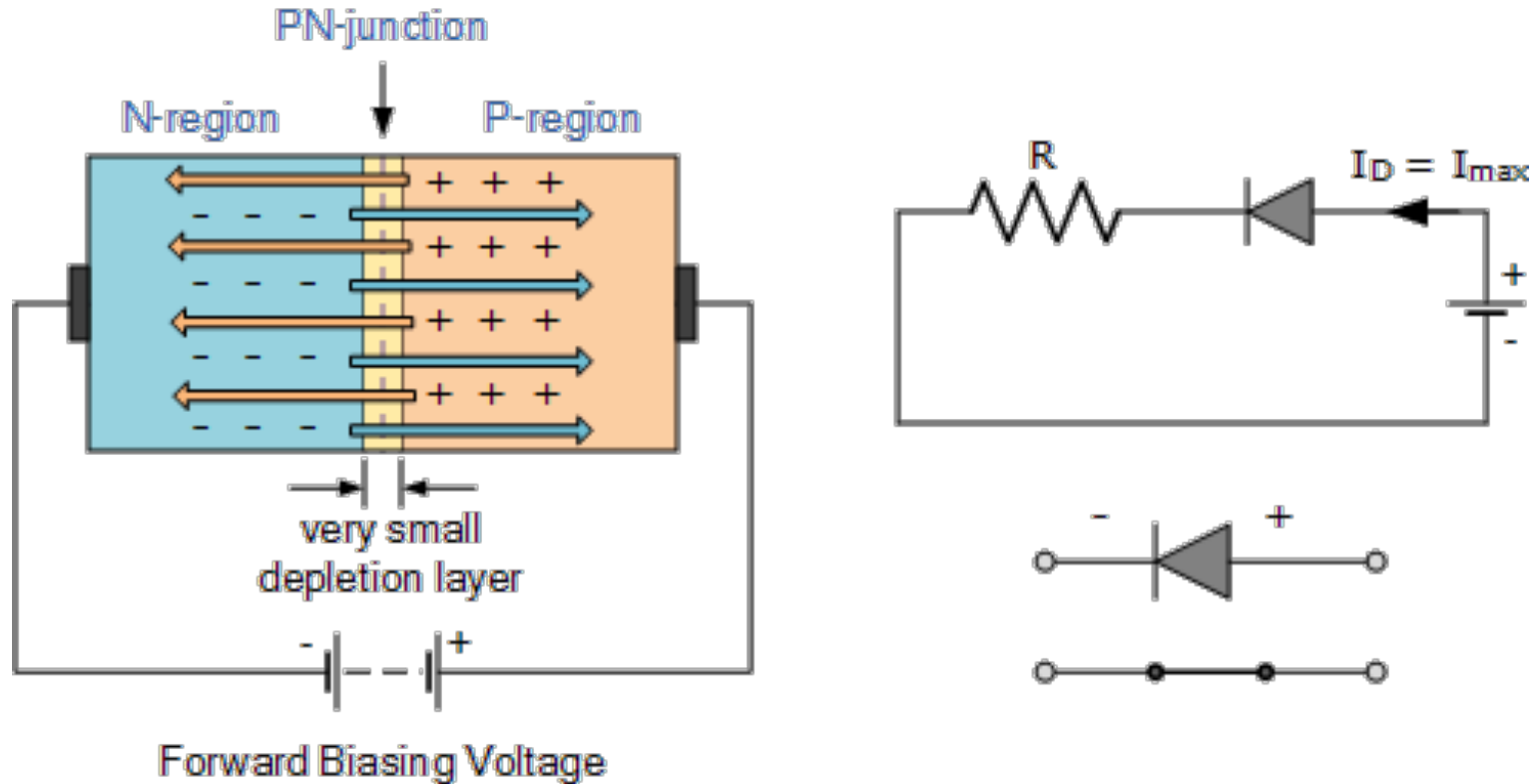


Current-voltage response for reverse bias

Hard for current to flow...

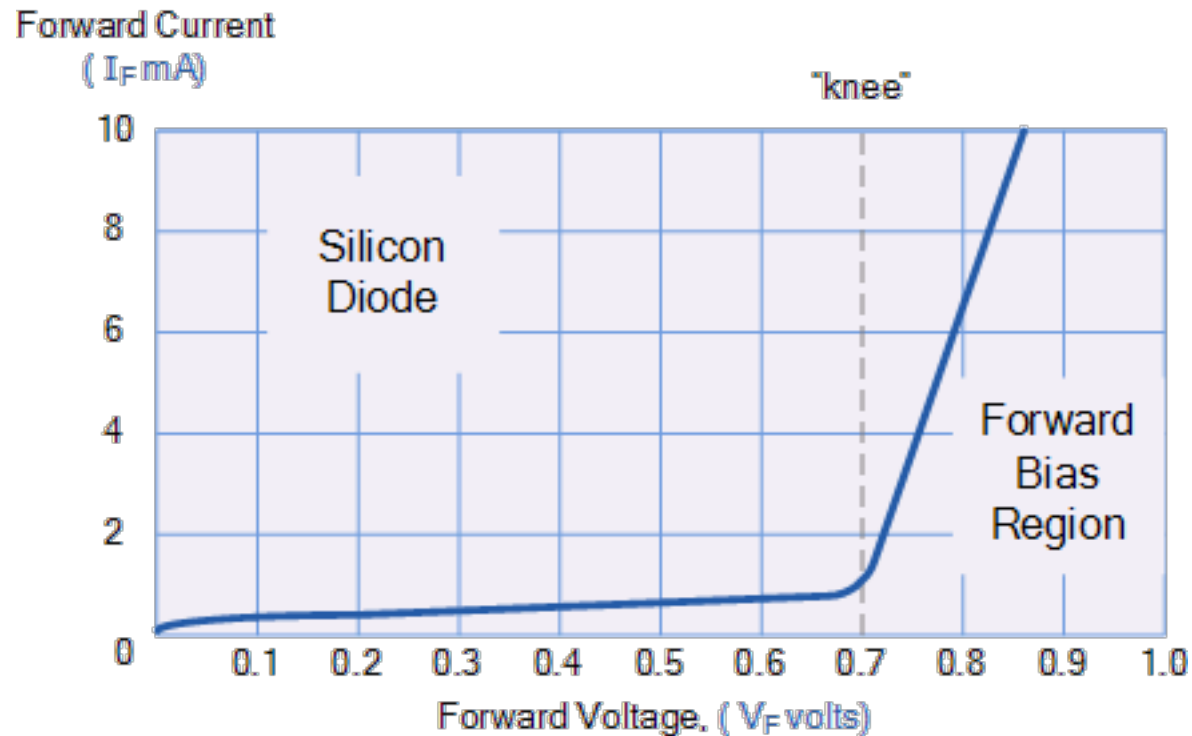


Canceling out natural bias (i.e. “Forward Bias”) Causes current to flow!



Forward bias reduces width of depletion zone & “injects” minority carriers (i.e. holes in N-region, Electrons in P-region) which can then diffuse thru that zone

Current-voltage response forward bias

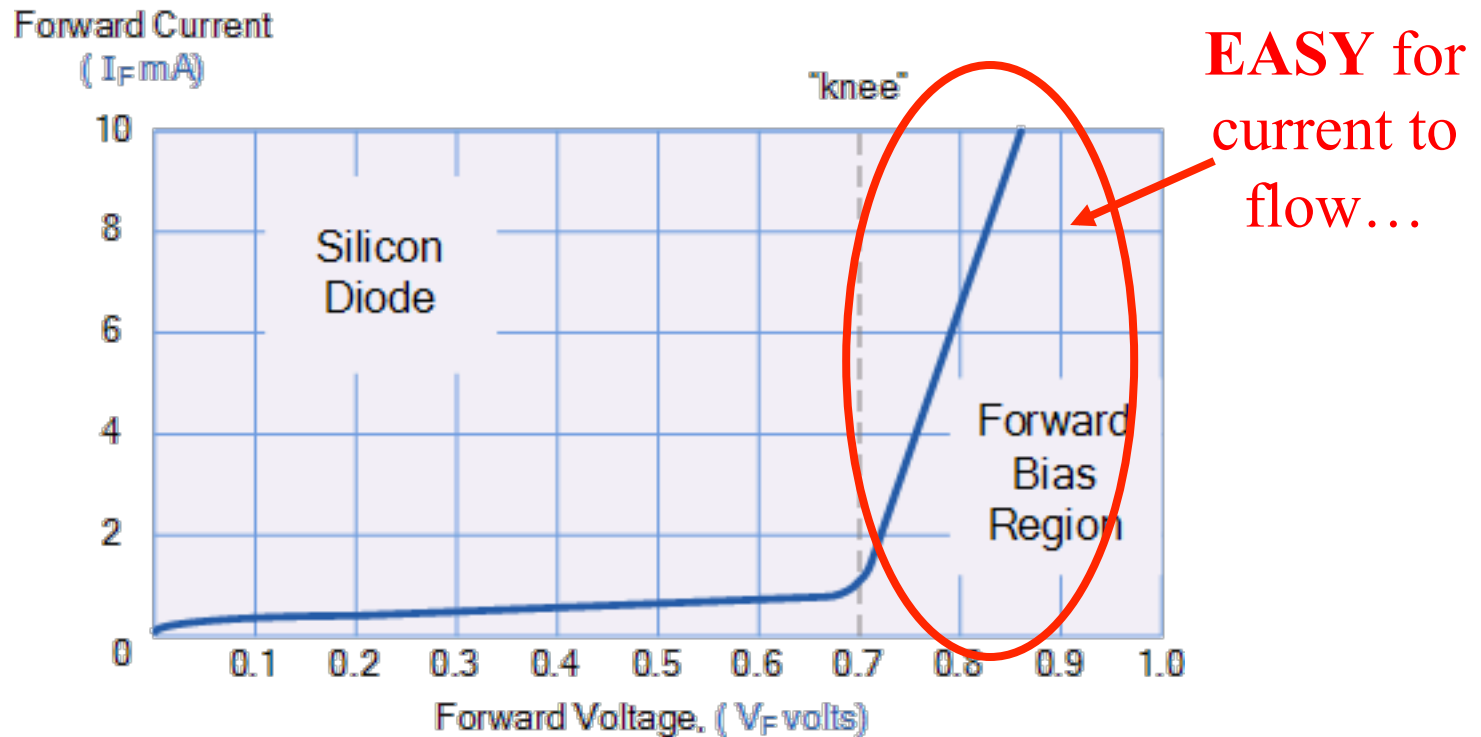


When forward bias voltage reaches or exceeds the Natural bias of the p-n junction, large current can

Begin to flow

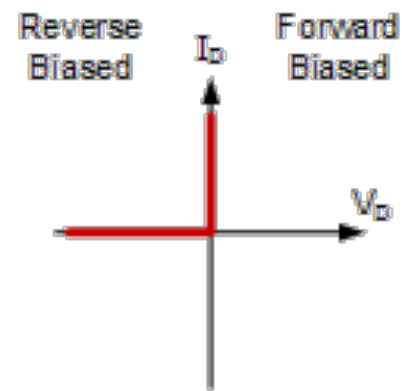
<http://www.electronics-tutorials.ws/diode>

Current-voltage response forward bias

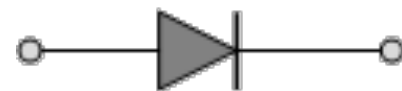


When forward bias voltage reaches or exceeds the natural bias of the p-n junction, large current begins to flow

Diode current-voltage characteristics



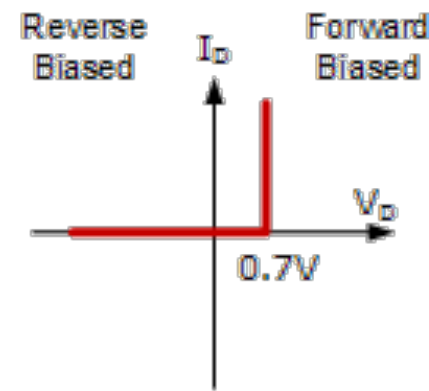
Ideal Diode



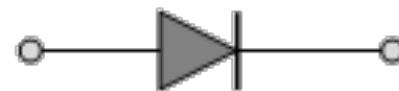
Forward Biased



Reverse Biased



Real Diode



Forward Biased



Reverse Biased